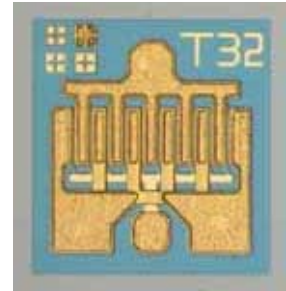


Low Noise and Medium Power GaAs FETs

FEATURES

- Via holes for source grounding
- Low Noise Figure: NF = 0.8dB Typical at 12 GHz
- High Associated Gain: Ga = 13 dB Typical at 12 GHz
- High Dynamic Range: 1 dB Compression Power $P_{1dB} = 24.5$ dBm at 12 GHz
- Breakdown Voltage: $BV_{DGO} \geq 9$ V
- $L_g = 0.25 \mu\text{m}$, $W_g = 600 \mu\text{m}$
- All-Gold Metallization for High Reliability
- Tight V_p ranges control
- High RF input power handling capability
- 100 % DC Tested

PHOTO ENLARGEMENT



DESCRIPTION

The TC1304V is the same as TC1304 expect via holes in the source pads for reducing the grounding inductance. The device is processed with via-holes for high gain applications. It can be used in circuits up to 30 GHz and suitable for low noise and medium power amplifier applications including a wide range of commercial and military applications. All devices are 100% DC tested to assure consistent quality. All bond pads are gold plated for either thermo-compression or thermo-sonic wire bonding.

ELECTRICAL SPECIFICATIONS ($T_A=25^\circ\text{C}$)

Symbol	Conditions	MIN	TYP	MAX	UNIT
NF	Noise Figure at $V_{DS} = 4$ V, $I_{DS} = 50$ mA, $f = 12$ GHz		0.8	1.0	dB
G_a	Associated Gain at $V_{DS} = 4$ V, $I_{DS} = 50$ mA, $f = 12$ GHz	11	13		dB
P_{1dB}	Output Power at 1dB Gain Compression Point, $f = 12$ GHz $V_{DS} = 6$ V, $I_{DS} = 80$ mA	23.5	24.5		dBm
G_L	Linear Power Gain, $f = 12$ GHz, $V_{DS} = 6$ V, $I_{DS} = 80$ mA	9	10		dB
I_{DSS}	Saturated Drain-Source Current at $V_{DS} = 2$ V, $V_{GS} = 0$ V		180		mA
g_m	Transconductance at $V_{DS} = 2$ V, $V_{GS} = 0$ V		200		mS
V_p	Pinch-off Voltage at $V_{DS} = 2$ V, $I_D = 1.2$ mA		-1.0*		Volts
BV_{DGO}	Drain-Gate Breakdown Voltage at $I_{DGO} = 0.3$ mA	9	12		Volts
R_{th}	Thermal Resistance		48		$^\circ\text{C/W}$

Note: * For the tight control of the pinch-off voltage . TC1304V's are divided into 3 groups:

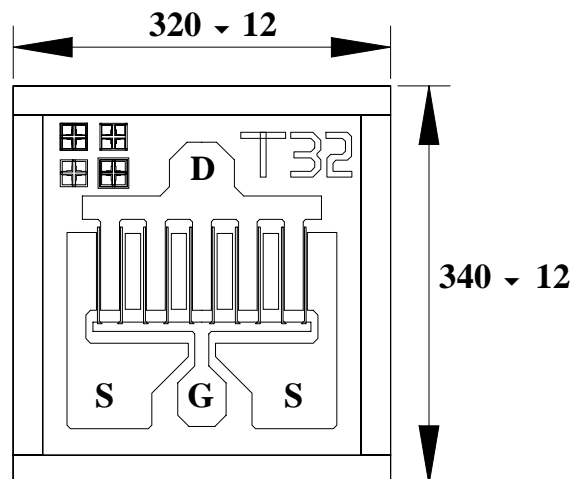
(1) **TC1304VP0710** : $V_p = -0.7$ V to -1.0 V (2) **TC1304VP0811** : $V_p = -0.8$ V to -1.1 V

(3) **TC1304VP0912** : $V_p = -0.9$ V to -1.2 V

In addition, the customers may specify their requirements.

ABSOLUTE MAXIMUM RATINGS (T_A=25 °C)

Symbol	Parameter	Rating
V _{DS}	Drain-Source Voltage	7.0 V
V _{GS}	Gate-Source Voltage	-3.0 V
I _{DS}	Drain Current	I _{DSS}
I _{GS}	Gate Current	600 μA
P _{in}	RF Input Power, CW	24 dBm
P _T	Continuous Dissipation	800 mW
T _{CH}	Channel Temperature	175 °C
T _{STG}	Storage Temperature	- 65 °C to +175 °C

CHIP DIMENSIONS


Units: Micrometers
Chip Thickness: 50

Gate Pad: 75 x 70
Drain Pad: 80 x 70
Source Pad: 75 x 80

CHIP HANDLING

DIE ATTACHMENT: Conductive epoxy or eutectic die attach is recommended. For eutectic die attach can be accomplished with Au-Sn (80%Au-20%Sn) perform in State Temperature: 290°C ± 5°C ; Handling Tool : Tweezers ; Time: less than 1min .

WIRE BONDING: The recommended wire bond method is thermo-compression bonding with 0.7 or 1.0 mil (0.018 or 0.025mm) gold wire. Stage Temperature: 220°C to 250°C ; Bond Tip Temperature : 150°C ; Bond Force: 20 to 30 gms depending on size of wire and Bond Tip Temperature.

HANDLING PRECAUTIONS: The user must operate in a clean, dry environment. Care should be exercised during handling avoid damage to the devices. Electrostatic Discharge (ESD) precautions should be observed at all stages of storage, handling, assembly, and testing. The static discharge must be less than 300V.